

# Silicon Carbide (SiC) Schottky Diode - EliteSiC, 8 A, 650 V, D2, D2PAK-2L

# FFSB0865B

Silicon Carbide (SiC) Schottky Diodes use a completely new technology that provides superior switching performance and higher reliability compared to Silicon. No reverse recovery current, temperature independent switching characteristics, and excellent thermal performance sets Silicon Carbide as the next generation of power semiconductor. System benefits include highest efficiency, faster operating frequency, increased power density, reduced EMI, and reduced system size and cost.

#### **Features**

- Max Junction Temperature 175°C
- Avalanche Rated 33 mJ
- High Surge Current Capacity
- Positive Temperature Coefficient
- Ease of Paralleling
- No Reverse Recovery / No Forward Recovery
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

#### **Applications**

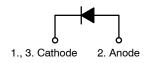
- · General Purpose
- SMPS, Solar Inverter, UPS
- Power Switching Circuits

#### MAXIMUM RATINGS (T<sub>J</sub> = 25°C unless otherwise noted)

Parameter	Symbol	Value	Unit		
Peak Repetitive Reverse Voltage	$V_{RRM}$	650	V		
Single Pulse Avalanche Energy ( $I_{L(pk)} = 11.5 \text{ A}, L = 0.5 \text{ mH}, V = 50$	E <sub>AS</sub>	33	mJ		
Continuous Rectified Forward Current	@ T <sub>C</sub> < 147	I <sub>F</sub>	8.0	Α	
Current	@ T <sub>C</sub> < 135		10.1		
Non-Repetitive Peak Forward Surge Current	$T_C = 25^{\circ}C$ $t_P = 10 \mu s$	I <sub>FM</sub>	577	Α	
	$T_{C} = 150^{\circ}C$ $t_{P} = 10 \ \mu s$		533		
Non-Repetitive Forward Surge Current (Half-Sine Pulse)	$T_C = 25$ °C $t_P = 8.3$ ms	I <sub>FSM</sub>	56	Α	
Power Dissipation	T <sub>C</sub> = 25°C	P <sub>tot</sub>	73	W	
	T <sub>C</sub> = 150°C		12		
Operating Junction and Storage T Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	°C		

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

V <sub>RRM</sub>	I <sub>F</sub>
650 V	8.0 A

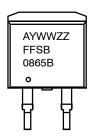


**Schottky Diode** 



D<sup>2</sup>PAK2 (TO-263-2L) CASE 418BK

#### **MARKING DIAGRAM**



A = Assembly Plant Code
YWW = Date Code (Year & Week)
ZZ = Lot Code
FFSB0865B = Specific Device Code

#### ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

### FFSB0865B

#### THERMAL CHARACTERISTICS

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case, Max.		2.05	°C/W

# **ELECTRICAL CHARACTERISTICS** (T<sub>J</sub> = 25°C unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit
ON CHARACTERISTICS	•		•	•	•	
Forward Voltage	V <sub>F</sub>	I <sub>F</sub> = 8.0 A, T <sub>J</sub> = 25°C	-	1.39	1.7	V
		I <sub>F</sub> = 8.0 A, T <sub>J</sub> = 125°C	-	1.55	2.0	
		I <sub>F</sub> = 8.0 A, T <sub>J</sub> = 175°C	-	1.71	2.4	1
Reverse Current	I <sub>R</sub>	V <sub>R</sub> = 650 V, T <sub>J</sub> = 25°C	-	0.5	40	μΑ
		V <sub>R</sub> = 650 V, T <sub>J</sub> = 125°C	-	1.0	80	1
		V <sub>R</sub> = 650 V, T <sub>J</sub> = 175°C	-	2.0	160	1
CHARGES, CAPACITANCES &	GATE RESISTANCE		•	•	•	
Total Capacitive Charge	$Q_{\mathbb{C}}$	V <sub>C</sub> = 400 V	-	22	_	nC
	C <sub>tot</sub>	V <sub>R</sub> = 1 V, f = 100 kHz	-	336	-	pF
		V <sub>B</sub> = 200 V, f = 100 kHz	_	39	_	1

 $V_{R} = 400 \text{ V}, \text{ f} = 100 \text{ kHz} \\ - 30 \\ - \\ \text{Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.}$ 

#### PACKAGE MARKING AND ORDERING INFORMATION

Part Number	Top Marking	Package	Packing Method <sup>†</sup>	Reel Size	Tape Width	Quantity
FFSB0865B	FFSB0865B	D <sup>2</sup> PAK2 (TO-263-2L)	Tape & Reel	330 mm	24 mm	800 Units

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, <a href="https://example.com/BRD8011/D">BRD8011/D</a>.

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# **TYPICAL CHARACTERISTICS**

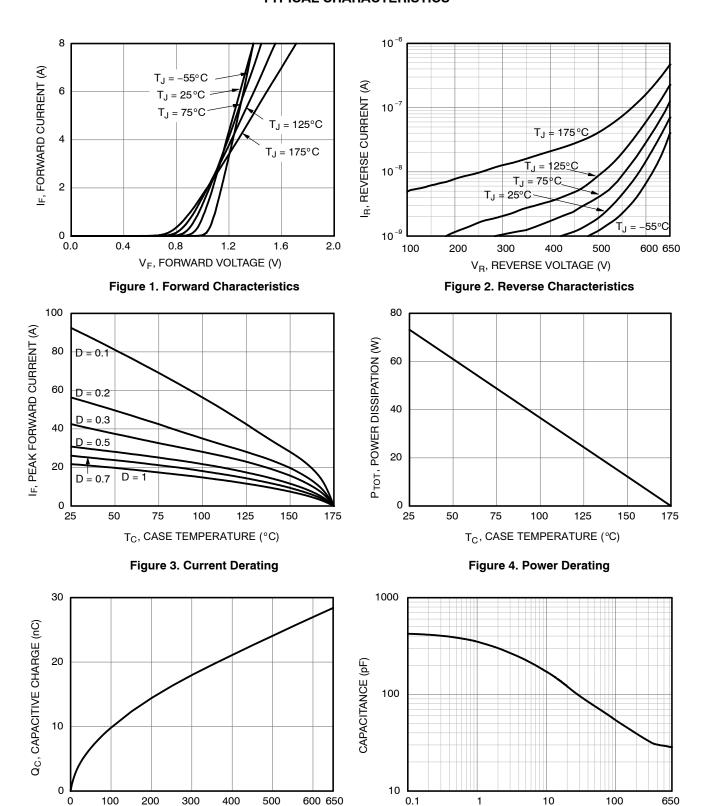


Figure 5. Capacitive Charge vs. Reverse Voltage

V<sub>R</sub>, REVERSE VOLTAGE (V)

 $\label{eq:VR} {\sf V}_{\sf R}, \, {\sf REVERSE} \, \, {\sf VOLTAGE} \, \, ({\sf V})$  Figure 6. Capacitance vs. Reverse Voltage

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# **TYPICAL CHARACTERISTICS**

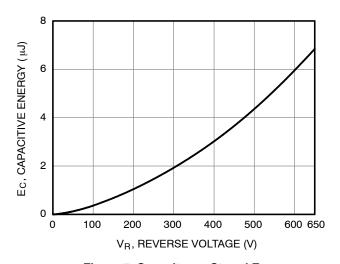


Figure 7. Capacitance Stored Energy

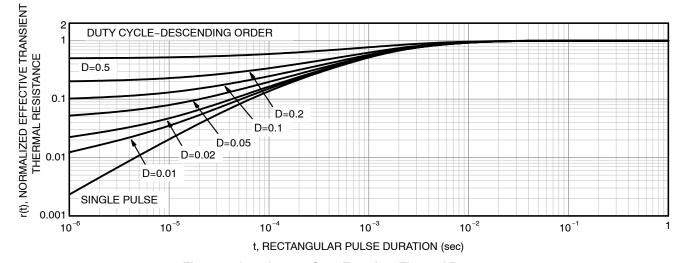
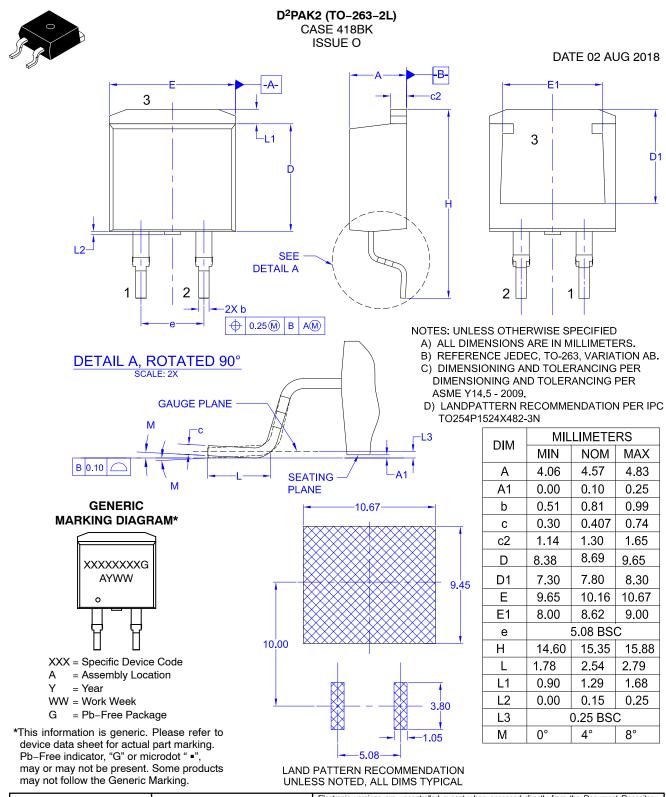


Figure 8. Junction-to-Case Transient Thermal Response



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DESCRIPTION:	D <sup>2</sup> PAK2 (TO-263-2L)		PAGE 1 OF 1	

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